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semiconductor and (light adj emitting) and (mask with (growth adj suppress\$))	0

Database:

US Patents Full-Text Database
US Pre-Grant Publication Full-Text Database
JPO Abstracts Database
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IBM Technical Disclosure Bulletins

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L6

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result set

DB=DWPI; PLUR=YES; OP=ADJ

L1 semiconductor and (light adj emitting) and (mask with (growth adj suppress\$))

0 L1

DB=TDBD; PLUR=YES; OP=ADJ

L2 semiconductor and (light adj emitting) and (mask with (growth adj suppress\$))

0 L2

DB=USPT; PLUR=YES; OP=ADJ

L3 semiconductor and (light adj emitting) and (mask with (growth adj suppress\$))

4 L3

DB=PGPB; PLUR=YES; OP=ADJ

L4 semiconductor and (light adj emitting) and (mask with (growth adj suppress\$))

8 L4

DB=JPAB; PLUR=YES; OP=ADJ

L5 semiconductor and (light adj emitting) and (mask with (growth adj suppress\$))

1 L5

DB=EPAB; PLUR=YES; OP=ADJ

L6 semiconductor and (light adj emitting) and (mask with (growth adj suppress\$))

0 L6

END OF SEARCH HISTORY

WEST[Generate Collection](#)[Print](#)**Search Results - Record(s) 1 through 4 of 4 returned.**☐ 1. Document ID: US 6566231 B2

L3: Entry 1 of 4

File: USPT

May 20, 2003

US-PAT-NO: 6566231

DOCUMENT-IDENTIFIER: US 6566231 B2

TITLE: Method of manufacturing high performance semiconductor device with reduced lattice defects in the active region

DATE-ISSUED: May 20, 2003

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Ogawa; Masahiro	Osaka			JP
Orita; Kenji	Osaka			JP
Ishida; Masahiro	Osaka			JP
Nakamura; Shinji	Osaka			JP
Imafuji; Osamu	Osaka			JP
Yuri; Masaaki	Osaka			JP

US-CL-CURRENT: 438/448; 438/42

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWIC
Draw Desc	Image										

☐ 2. Document ID: US 6380051 B1

L3: Entry 2 of 4

File: USPT

Apr 30, 2002

US-PAT-NO: 6380051

DOCUMENT-IDENTIFIER: US 6380051 B1

TITLE: Layered structure including a nitride compound semiconductor film and method for making the same

DATE-ISSUED: April 30, 2002

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Yuasa; Takayuki	Nara-ken			JP
Ueta; Yoshihiro	Tenri			JP

US-CL-CURRENT: 438/481; 257/E21.131, 438/478

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWIC
Draw Desc	Image										

☐ 3. Document ID: US 6294440 B1

L3: Entry 3 of 4

File: USPT

Sep 25, 2001

US-PAT-NO: 6294440

DOCUMENT-IDENTIFIER: US 6294440 B1

TITLE: Semiconductor substrate, light-emitting device, and method for producing the same

DATE-ISSUED: September 25, 2001

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Tsuda; Yuhzoh	Tenri			JP
Ito; Shigetoshi	Ikoma			JP
Yano; Seiki	Yamatokoriyama			JP

US-CL-CURRENT: 438/479

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWC
Draw Desc	Image										

☐ 4. Document ID: US 4935936 A

L3: Entry 4 of 4

File: USPT

Jun 19, 1990

US-PAT-NO: 4935936

DOCUMENT-IDENTIFIER: US 4935936 A

TITLE: Semiconductor structure with flared mesa burying layers

DATE-ISSUED: June 19, 1990

INVENTOR-INFORMATION:

NAME	CITY	STATE	ZIP CODE	COUNTRY
Nelson; Andrew W.	Felixstowe			GB2
Hobbs; Richard E.	Bredfield			GB2
Devlin; W. John	Ipswich			GB2
Lenton; Charles G.	Eye			GB2

US-CL-CURRENT: 372/46

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KWC
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semiconductor and (light adj emitting) and (mask with (growth adj suppress\$))	4

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☐ 1. Document ID: US 20030047746 A1

L4: Entry 1 of 8

File: PGPB

Mar 13, 2003

PGPUB-DOCUMENT-NUMBER: 20030047746
PGPUB-FILING-TYPE: new
DOCUMENT-IDENTIFIER: US 20030047746 A1

TITLE: GaN substrate formed over GaN layer having discretely formed minute holes produced by use of discretely arranged growth suppression mask elements

PUBLICATION-DATE: March 13, 2003

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Kuniyasu, Toshiaki	Kaisei-machi		JP	
Wada, Mitsugu	Kaisei-machi		JP	
Fukunaga, Toshiaki	Kaisei-machi		JP	

US-CL-CURRENT: 257/103; 257/15, 372/45, 438/22

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWIC
Draw Desc	Image										

☐ 2. Document ID: US 20030030053 A1

L4: Entry 2 of 8

File: PGPB

Feb 13, 2003

PGPUB-DOCUMENT-NUMBER: 20030030053
PGPUB-FILING-TYPE: new
DOCUMENT-IDENTIFIER: US 20030030053 A1

TITLE: Nitride semiconductor device and fabrication method thereof

PUBLICATION-DATE: February 13, 2003

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Kawakami, Toshiyuki	Tenri-Shi		JP	
Yamasaki, Yukio	Osaka		JP	
Ito, Shigetoshi	Ikoma-Shi		JP	
Omi, Susumu	Osaka		JP	

US-CL-CURRENT: 257/72

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWIC
Draw Desc	Image										

☐ 3. Document ID: US 20020098641 A1

L4: Entry 3 of 8

File: PGPB

Jul 25, 2002

PGPUB-DOCUMENT-NUMBER: 20020098641
PGPUB-FILING-TYPE: new
DOCUMENT-IDENTIFIER: US 20020098641 A1

TITLE: Semiconductor substrate, light-emitting device, and method for producing the same

PUBLICATION-DATE: July 25, 2002

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Tsuda, Yuhzoh	Tenri-shi		JP	
Ito, Shigetoshi	Ikoma-shi		JP	
Yano, Seiki	Yamatokoriyama-shi		JP	

US-CL-CURRENT: 438/241

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWC
Draw	Desc	Image									

☐ 4. Document ID: US 20020064195 A1

L4: Entry 4 of 8

File: PGPB

May 30, 2002

PGPUB-DOCUMENT-NUMBER: 20020064195
PGPUB-FILING-TYPE: new
DOCUMENT-IDENTIFIER: US 20020064195 A1

TITLE: Semiconductor laser, semiconductor device and nitride series III-V group compound substrate, as well as manufacturing method thereof

PUBLICATION-DATE: May 30, 2002

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Takeya, Motonobu	Miyagi		JP	
Yanashima, Katsunori	Kanagawa		JP	
Asano, Takeharu	Miyagi		JP	
Goto, Osamu	Miyagi		JP	
Ikeda, Shinro	Miyagi		JP	
Shibuya, Katsuyoshi	Miyagi		JP	
Hino, Tomonori	Miyagi		JP	
Kijima, Satoru	Miyagi		JP	
Ikeda, Masao	Kanagawa		JP	

US-CL-CURRENT: 372/45

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWC
Draw	Desc	Image									

☐ 5. Document ID: US 20020048964 A1

L4: Entry 5 of 8

File: PGPB

Apr 25, 2002

PGPUB-DOCUMENT-NUMBER: 20020048964
PGPUB-FILING-TYPE: new
DOCUMENT-IDENTIFIER: US 20020048964 A1

TITLE: A LAYERED STRUCTURE INCLUDING A NITRIDE COMPOUND SEMICONDUCTOR FILM AND
METHOD FOR MAKING THE SAME

PUBLICATION-DATE: April 25, 2002

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
YUASA, TAKAYUKI	IKOMA-GUN		JP	
UETA, YOSHIHIRO	TENRI-SHI		JP	

US-CL-CURRENT: 438/763; 257/82, 438/767, 438/791

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

KMIC

☐ 6. Document ID: US 20020014629 A1

L4: Entry 6 of 8

File: PGPB

Feb 7, 2002

PGPUB-DOCUMENT-NUMBER: 20020014629
PGPUB-FILING-TYPE: new
DOCUMENT-IDENTIFIER: US 20020014629 A1

TITLE: Group III nitride compound semiconductor device and method for producing the
same

PUBLICATION-DATE: February 7, 2002

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Shibata, Naoki	Nishikasugai-gun		JP	
Chiyo, Toshiaki	Nishikasugai-gun		JP	
Senda, Masanobu	Nishikasugai-gun		JP	
Ito, Jun	Nishikasugai-gun		JP	
Watanabe, Hiroshi	Nishikasugai-gun		JP	
Asami, Shinya	Nishikasugai-gun		JP	
Asami, Shizuyo	Nishikasugai-gun		JP	

US-CL-CURRENT: 257/79; 257/E33.028, 438/22

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
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KMIC

☐ 7. Document ID: US 20010039104 A1

L4: Entry 7 of 8

File: PGPB

Nov 8, 2001

PGPUB-DOCUMENT-NUMBER: 20010039104
PGPUB-FILING-TYPE: new
DOCUMENT-IDENTIFIER: US 20010039104 A1

TITLE: Semiconductor substrate, light-emitting device, and method for producing the same

PUBLICATION-DATE: November 8, 2001

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Tsuda, Yuhzoh	Tenri-shi		JP	
Ito, Shingetoshi	Ikoma-shi		JP	
Yano, Seiki	Yamatokoriyama-shi		JP	

US-CL-CURRENT: 438/496

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KMC
Draw	Desc	Image								

☐ 8. Document ID: US 20010029086 A1

L4: Entry 8 of 8

File: PGPB

Oct 11, 2001

PGPUB-DOCUMENT-NUMBER: 20010029086
PGPUB-FILING-TYPE: new
DOCUMENT-IDENTIFIER: US 20010029086 A1

TITLE: Semiconductor device, method for fabricating the same and method for fabricating semiconductor substrate

PUBLICATION-DATE: October 11, 2001

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Ogawa, Masahiro	Osaka		JP	
Orita, Kenji	Osaka		JP	
Ishida, Masahiro	Osaka		JP	
Nakamura, Shinji	Osaka		JP	
Imafuji, Osamu	Osaka		JP	
Yuri, Masaaki	Osaka		JP	

US-CL-CURRENT: 438/448; 438/453

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KMC
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☐ 1. Document ID: JP 2002204035 A

L5: Entry 1 of 1

File: JPAB

Jul 19, 2002

DOCUMENT-IDENTIFIER: JP 2002204035 A

TITLE: NITRIDE SEMICONDUCTOR LIGHT EMITTING ELEMENT, AND DEVICE INCLUDING ITAbstract Text (1):

PROBLEM TO BE SOLVED: To improve a luminescence life and intensity of luminescence and to prevent a crack in a nitride semiconductor light emitting element.

Abstract Text (2):

SOLUTION: In the nitride semiconductor light emitting element, a mask pattern on one main face of the nitride semiconductor substrate functions as a growth suppressing film for suppressing the growth of the nitride semiconductor layer, and has a plurality of windows that is not covered with the growth suppressing film. There are two or more mask widths between adjacent windows, and the mask pattern includes a mask A group and each mask B group on both sides of the mask A group. The width of the mask A group is larger than that of the mask B group. The nitride semiconductor luminescent element has a light emitting element structure including the window, the nitride semiconductor base layer that covers the mask pattern, and a luminescent layer that includes a quantum well layer or the quantum well layer and the adjoining barrier layer. In this case, the current bottleneck through which the current is injected in the luminescent layer is formed at an upper part of the mask A.

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWIC
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semiconductor and (light adj emitting) and (mask with (growth adj suppress\$))	1

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